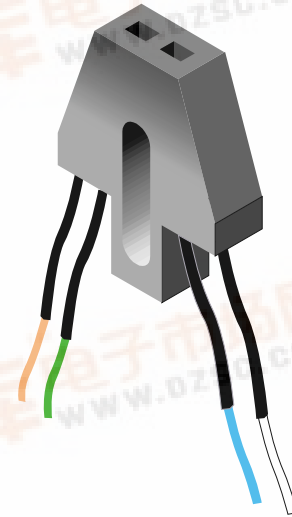
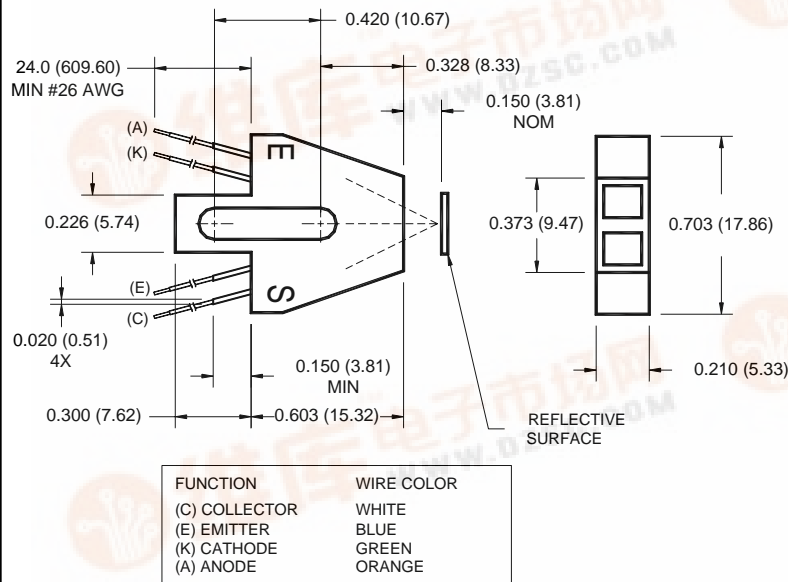
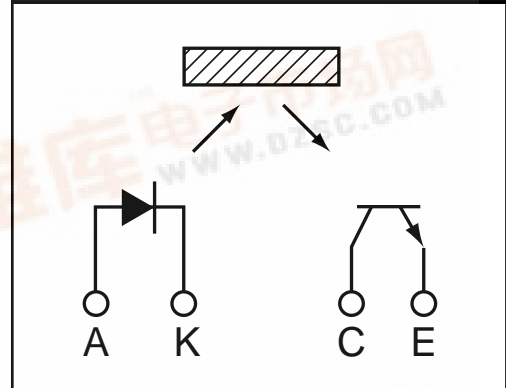


PACKAGE DIMENSIONS



SCHEMATIC



NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.

DESCRIPTION

The QRB1133/1134 consists of an infrared emitting diode and an NPN silicon phototransistor mounted side by side on a converging optical axis in a black plastic housing. The phototransistor responds to radiation from the emitting diode only when a reflective object passes within its field of view. The area of the optimum response approximates a circle .200" in diameter.

FEATURES

- Phototransistor output
- High Sensitivity
- Low cost plastic housing
- #26 AWG, 24 inch PVC wire termination
- Infrared transparent plastic covers for dust protection



QRB1133 QRB1134

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Units
Operating Temperature	T_{OPR}	-40 to +85	$^\circ\text{C}$
Storage Temperature	T_{STG}	-40 to +85	$^\circ\text{C}$
Soldering Temperature (Iron) ^(2,3,4)	$T_{\text{SOL-I}}$	240 for 5 sec	$^\circ\text{C}$
Soldering Temperature (Flow) ^(2,3)	$T_{\text{SOL-F}}$	260 for 10 sec	$^\circ\text{C}$
EMITTER			
Continuous Forward Current	I_F	50	mA
Reverse Voltage	V_R	5	V
Power Dissipation ⁽¹⁾	P_D	100	mW
SENSOR			
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector Voltage	V_{ECO}	50	V
Collector Current	I_C	20	mA
Power Dissipation ⁽¹⁾	P_D	100	mW

NOTES

- Derate power dissipation linearly 1.67 mW/ $^\circ\text{C}$ above 25 $^\circ\text{C}$.
- RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
- Soldering iron 1/16" (1.6mm) minimum from housing.
- D is the distance from the assembly face to the reflective surface.
- Measured using an Eastman Kodak neutral test card with 90% diffused reflecting surface.
- Cross talk is the photo current measured with current to the input diode and no reflecting surface.

ELECTRICAL / OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS
EMITTER						
Forward Voltage	$I_F = 40 \text{ mA}$	V_F	—	—	1.7	V
Reverse Current	$V_R = 2.0 \text{ V}$	I_R	—	—	100	μA
Peak Emission Wavelength	$I_F = 20 \text{ mA}$	λ_{PE}	—	940	—	nm
SENSOR						
Collector-Emitter Breakdown Voltage	$I_C = 1 \text{ mA}$	BV_{CEO}	30	—	—	V
Emitter-Collector Breakdown Voltage	$I_E = 0.1 \text{ mA}$	BV_{ECO}	5	—	—	V
Collector-Emitter Dark Current	$V_{\text{CE}} = 10 \text{ V}, I_F = 0 \text{ mA}$	I_{CEO}	—	—	100	nA
COUPLED						
On-state Collector Current	$I_F = 40 \text{ mA}, V_{\text{CE}} = 5 \text{ V}$ $D = .150^{(5,6)}$	$I_{\text{C(ON)}}$	0.20	—	—	mA
			0.60	—	—	
Collector-Emitter Saturation Voltage	$I_F = 20 \text{ mA}, I_C = 0.5 \text{ mA}$	$V_{\text{CE(SAT)}}$	—	—	0.4	V
Rise Time	$V_{\text{CE}} = 5 \text{ V}, R_L = 100 \Omega$	t_r	—	8	—	μs
Fall Time	$I_{\text{C(ON)}} = 5 \text{ mA}$	t_f	—	8	—	μs
Cross Talk	$I_F = 40 \text{ mA}, V_{\text{CE}} = 5 \text{ V}^{(7)}$	I_{CX}	—	—	1.00	μA

TYPICAL PERFORMANCE CURVES

Fig. 1 Forward Voltage vs. Forward Current

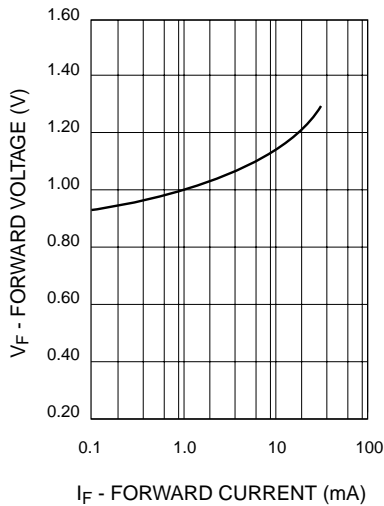


Fig. 2 Normalized Collector Current vs. Forward Current

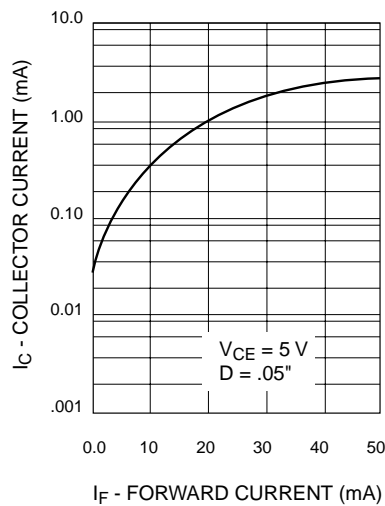


Fig. 3 Normalized Collector Current vs. Temperature

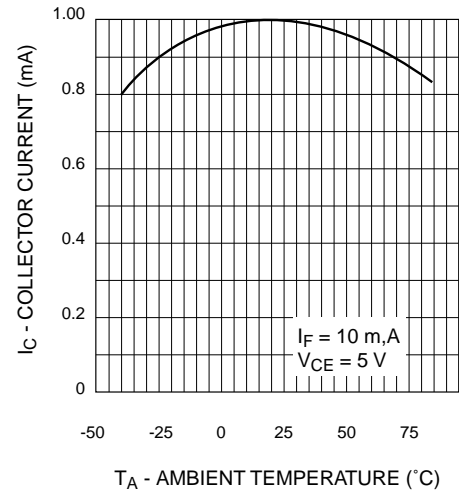


Fig. 4 Normalized Collector Dark Current vs. Temperature

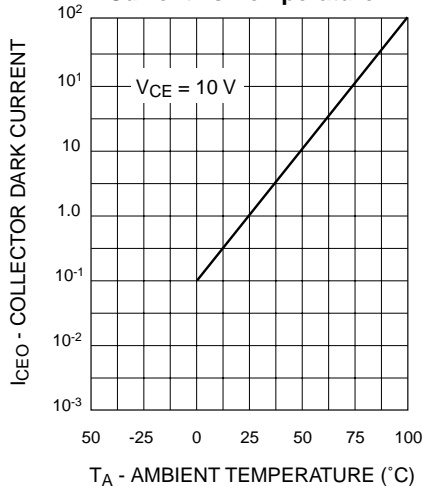
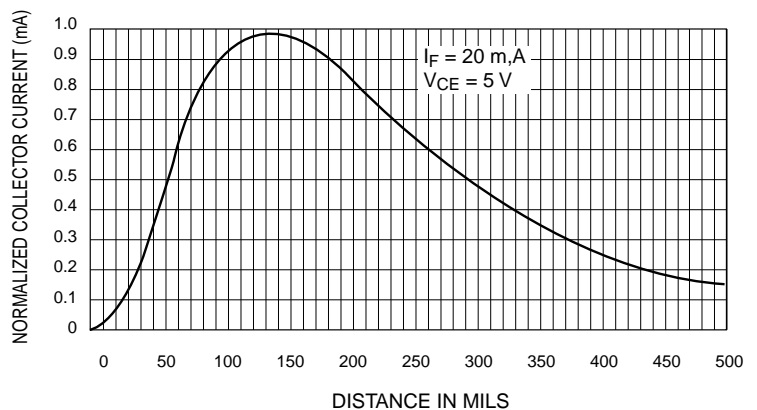


Fig. 5 Normalized Collector Current vs. Distance





PHOTOTRANSISTOR REFLECTIVE OBJECT SENSORS

QRB1133 QRB1134

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.